

## IR MOSFET-DirectFET™

IRF7749L1TRPbF

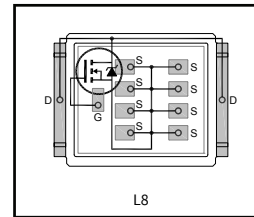
Quality Requirement Category: Industrial

### Applications

- RoHS Compliant, Halogen Free
- Lead-Free (Qualified up to 260°C Reflow)
- Ideal for High Performance Isolated Converter Primary Switch Socket
- Optimized for Synchronous Rectification
- Low Conduction Losses
- High Cdv/dt Immunity
- Low Profile (<0.7mm)
- Dual Sided Cooling Compatible
- Compatible with existing Surface Mount Techniques

DirectFET™ N-Channel Power MOSFET

<b>V<sub>DSS</sub></b>	<b>60V</b>
<b>R<sub>DS(on)</sub> typ. @ V<sub>GS</sub> = 10V</b>	<b>1.1mΩ</b>
<b>R<sub>DS(on)</sub> max @ V<sub>GS</sub> = 10V</b>	<b>1.5mΩ</b>
<b>I<sub>D</sub> (Silicon Limited)</b>	<b>345A ⑦</b>
<b>I<sub>D</sub> (Package Limited)</b>	<b>375A ①</b>



<b>G</b>	<b>D</b>	<b>S</b>
Gate	Drain	Source

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRF7749L1TRPbF	DirectFET™ Large Can (LA)	Tape and Reel	4000	IRF7749L1TRPbF

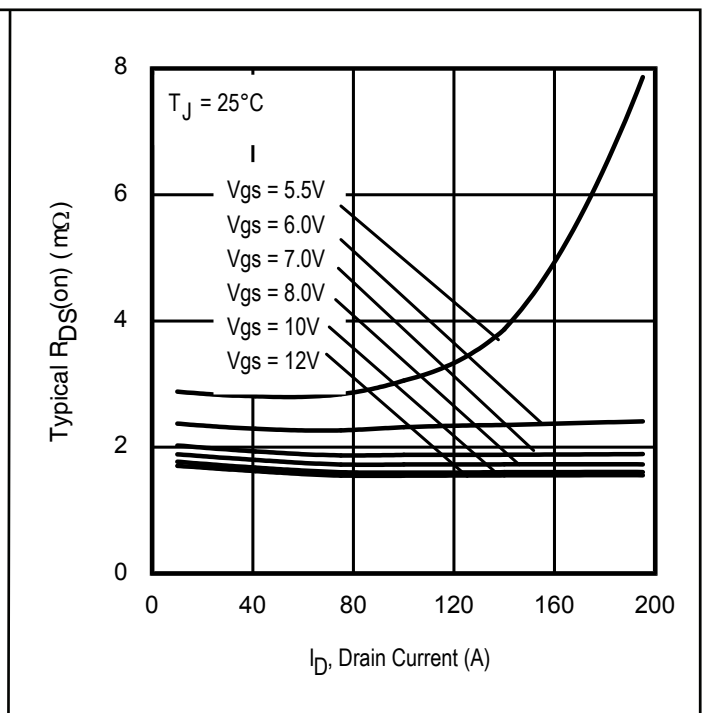
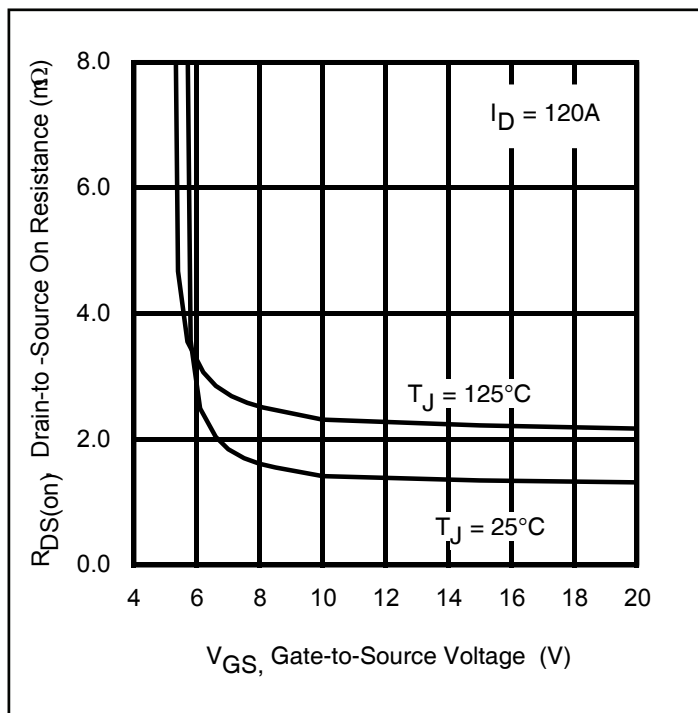


Figure 1 Typical On-Resistance vs. Gate Voltage


Figure 2 Typical On-Resistance vs. Drain Current

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## 1 Parameters

**Table1** Key performance parameters

Parameter	Values	Units
$V_{DS}$	60	V
$R_{DS(on) max}$	1.5	m $\Omega$
$I_D @ T_C$	345 	A
$I_D @ T_A$	36	A

## 2 Maximum ratings and thermal characteristics

**Table 2 Maximum ratings (at  $T_J=25^\circ\text{C}$ , unless otherwise specified)**

Parameter	Symbol	Conditions	Values	Unit
Continuous Drain Current (Silicon Limited) ④	$I_D$	$T_C = 25^\circ\text{C}$ , $V_{GS} @ 10\text{V}$	345 ⑦	A
Continuous Drain Current (Silicon Limited) ④	$I_D$	$T_C = 100^\circ\text{C}$ , $V_{GS} @ 10\text{V}$	243	
Continuous Drain Current (Silicon Limited) ①	$I_D$	$T_A = 25^\circ\text{C}$ , $V_{GS} @ 10\text{V}$	36	
Continuous Drain Current (Package Limited) ④	$I_D$	$T_C = 25^\circ\text{C}$ , $V_{GS} @ 10\text{V}$	375 ①	
Pulsed Drain Current ②	$I_{DM}$	$T_C = 25^\circ\text{C}$	1380	W
Maximum Power Dissipation	$P_D$	$T_C = 25^\circ\text{C}$	341	
Maximum Power Dissipation	$P_D$	$T_A = 25^\circ\text{C}$	3.8	W/°C
Linear Derating Factor	-	-	0.025	
Gate-to-Source Voltage	$V_{GS}$	-	$\pm 20$	V
Operating Junction	$T_J$	-	-55 to +175	°C
Storage Temperature Range	$T_{STG}$	-		

**Table 3 Thermal characteristics**

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Junction-to-Ambient ①	$R_{\theta JA}$	-	-	-	40	°C/W
Junction-to-Ambient ③	$R_{\theta JA}$	-	-	12.5	-	
Junction-to-Ambient ②	$R_{\theta JA}$	-	-	20	-	
Junction-to-Case ④ ⑥	$R_{\theta JC}$	-	-	-	0.44	
Junction-to-PCB Mounted	$R_{\theta JA-PCB}$	-	-	-	0.5	

**Table 4 Avalanche characteristics**

Parameter	Symbol	Values	Unit
Single Pulse Avalanche Energy (Thermally Limited) ③	$E_{AS}$	315	mJ
Single Pulse Avalanche Energy (Tested) ③	$E_{AS}$	714	
Avalanche Current ②	$I_{AR}$	See Fig.15,16, 19a, 19b	A
Repetitive Avalanche Energy ②	$E_{AR}$		mJ

**Notes:**

- ① Package limit current based on source connection technology
- ② Repetitive rating; pulse width limited by max. junction temperature.
- ③ Limited by  $T_{Jmax}$ , starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.044\text{mH}$ ,  $R_G = 50\Omega$ ,  $I_{AS} = 120\text{A}$ ,  $V_{GS} = 10\text{V}$ .
- ④ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ⑤  $C_{oss}$  eff. (TR) is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .
- ⑥  $R_\theta$  is measured at  $T_J$  approximately  $90^\circ\text{C}$ .
- ⑦ Silicon limit current based on maximum allowable junction temperature  $T_{Jmax}$ .

### 3 Electrical characteristics

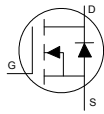
**Table 5 Static characteristics**

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	60	-	-	V
Breakdown Voltage Temp. Coefficient	$\Delta V_{(BR)DSS}/\Delta T_J$	Reference to 25°C, $I_D = 3.0mA$	-	56	-	mV/°C
Static Drain-to-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 120A$	-	1.1	1.5	mΩ
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0	-	4.0	V
Gate Threshold Voltage Coefficient	$\Delta V_{GS(th)}/\Delta T_J$		-	8.8	-	mV/°C
Drain-to-Source Leakage Current	$I_{DSS}$	$V_{DS} = 60V, V_{GS} = 0V$	-	-	20	μA
		$V_{DS} = 60V, V_{GS} = 0V, T_J = 125^\circ C$	-	-	250	
Gate-to-Source Forward Leakage	$I_{GSS}$	$V_{GS} = 20V$	-	-	100	nA
	$I_{GSS}$	$V_{GS} = -20V$	-	-	100	
Gate Resistance	$R_G$	-	-	1.5	-	Ω

**Table 6 Dynamic characteristics**

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Forward Trans conductance	gfs	$V_{DS} = 10V, I_D = 120A$	185	-	-	S
Total Gate Charge	$Q_g$	$I_D = 120A$ $V_{DS} = 30V$ $V_{GS} = 10V$ ④	-	183	275	nC
Gate-to-Source Charge	$Q_{gs1}$		-	39	-	
Gate-to-Source Charge	$Q_{gs2}$		-	19	-	
Gate-to-Drain ("Miller) Charge	$Q_{gd}$		-	46	-	
Gate Charge Overdrive	$Q_{godr}$		-	79	-	
Switch Charge ( $Q_{gs2} + Q_{gd}$ )	$Q_{sw}$		-	65	-	
Output Charge	$Q_{oss}$	$V_{DS} = 48V, V_{GS} = 0V$	-	119	-	nC
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 30V$	-	29	-	ns
Rise Time	$t_r$	$I_D = 120A$	-	149	-	
Turn-Off Delay Time	$t_{d(off)}$	$R_G = 1.8\Omega$	-	72	-	
Fall Time	$t_f$	$V_{GS} = 10V$ ④	-	88	-	
Input Capacitance	$C_{iss}$	$V_{GS} = 0V$	-	10655	-	pF
Output Capacitance	$C_{oss}$	$V_{DS} = 25V$	-	1627	-	
Reverse Transfer Capacitance	$C_{rss}$	$f = 1.0MHz$	-	680	-	
Effective Output Capacitance	$C_{oss\ eff.}$	$V_{GS} = 0V, V_{DS} = 0V\ to\ 48V$ ⑤	-	1959	-	

**Table 7 Reverse Diode**

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Continuous Source Current (Body Diode)	$I_S$	MOSFET symbol showing the integral reverse p-n junction diode. 	-	-	345	A
Pulsed Source Current (Body Diode) ②	$I_{SM}$		-	-	1380	
Diode Forward Voltage	$V_{SD}$	$T_J = 25^\circ C, I_S = 120A, V_{GS} = 0V$ ④	-	-	1.3	V
Reverse Recovery Time	$t_{rr}$	$T_J = 25^\circ C, I_F = 120A,$	-	42	-	ns
Reverse Recovery Charge	$Q_{rr}$	$V_{DD} = 30V, di/dt = 100A/\mu s$ ④	-	54	-	nC

### 4 Electrical characteristic diagrams

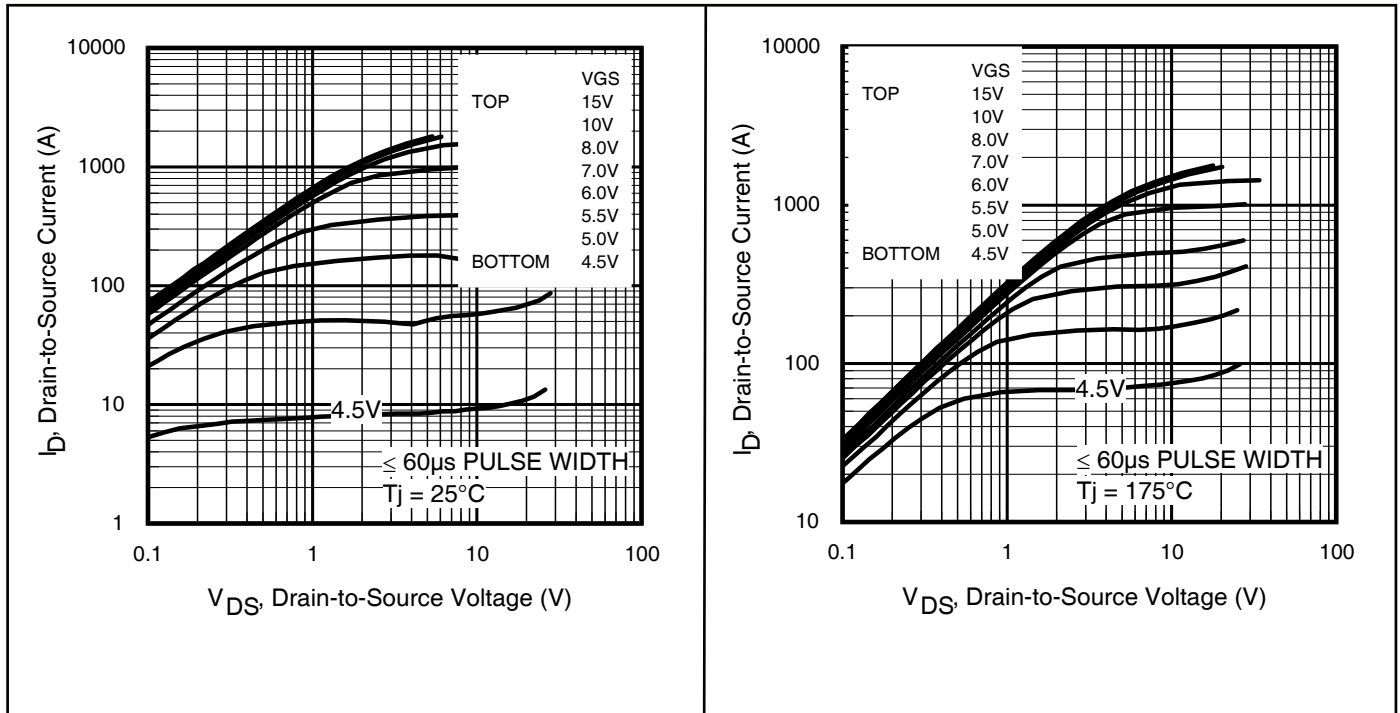


Figure 3 Typical Output Characteristics

Figure 4 Typical Output Characteristics

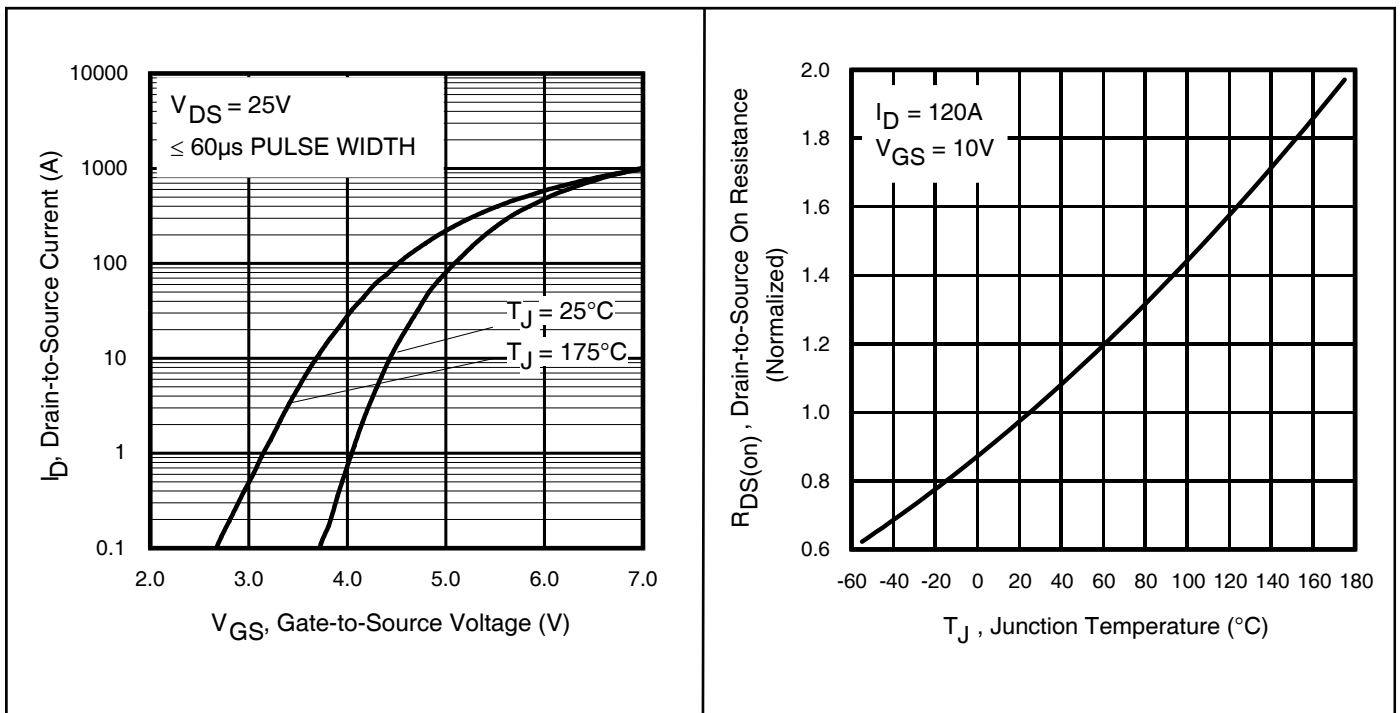


Figure 5 Typical Transfer Characteristics

Figure 6 Normalized On-Resistance vs. Temperature

Electrical characteristic diagrams

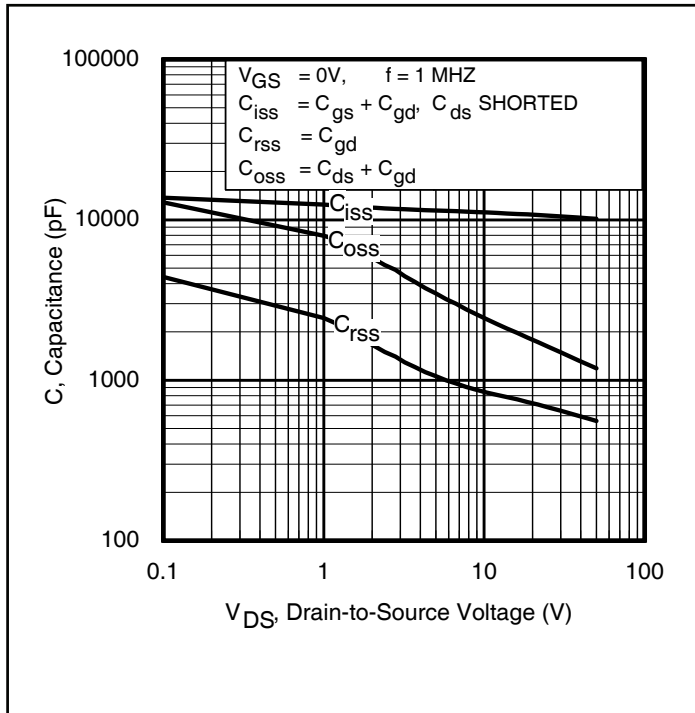


Figure 7 Typical Capacitance vs. Drain-to-Source Voltage

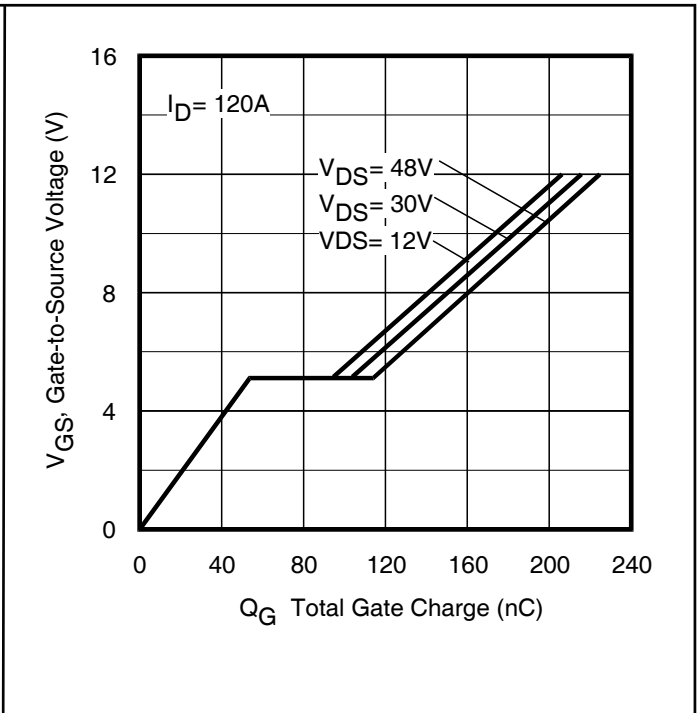


Figure 8 Typical Gate Charge vs. Gate-to-Source Voltage

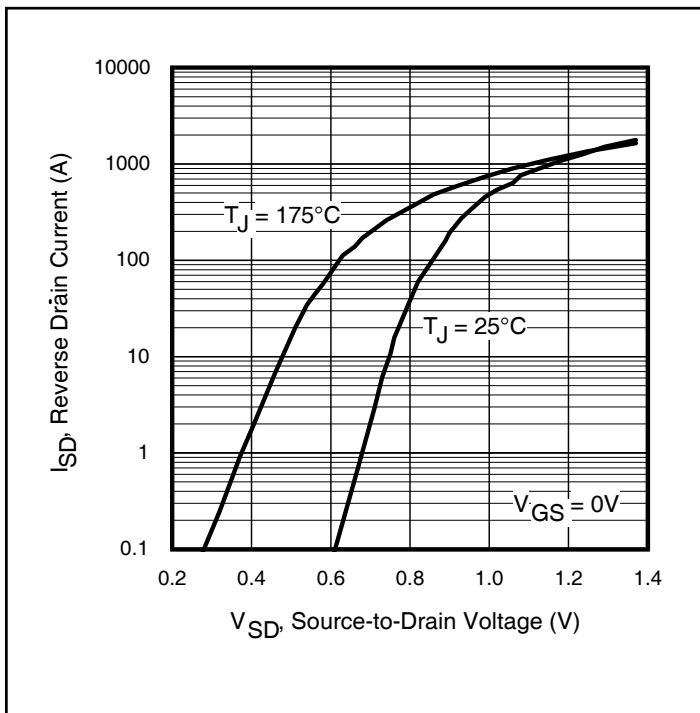


Figure 9 Typical Source-Drain Diode Forward Voltage

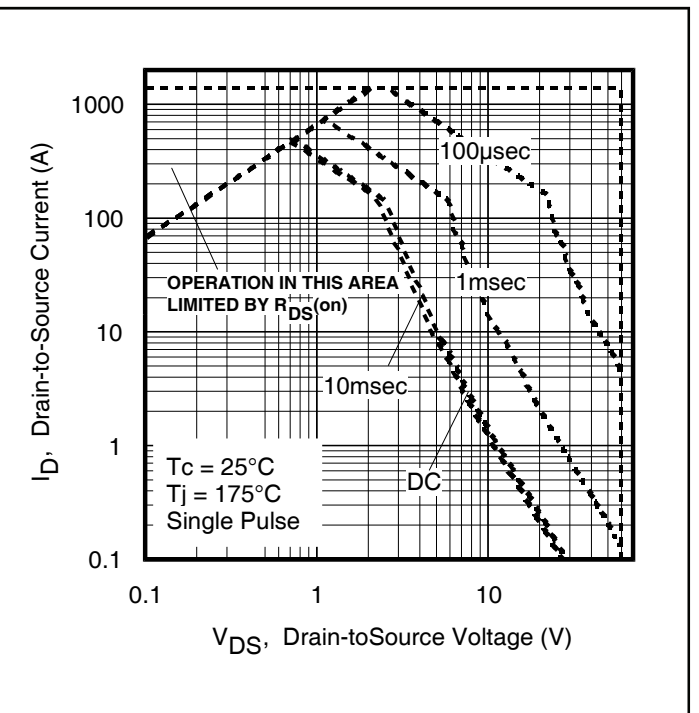


Figure 10 Maximum Safe Operating Area

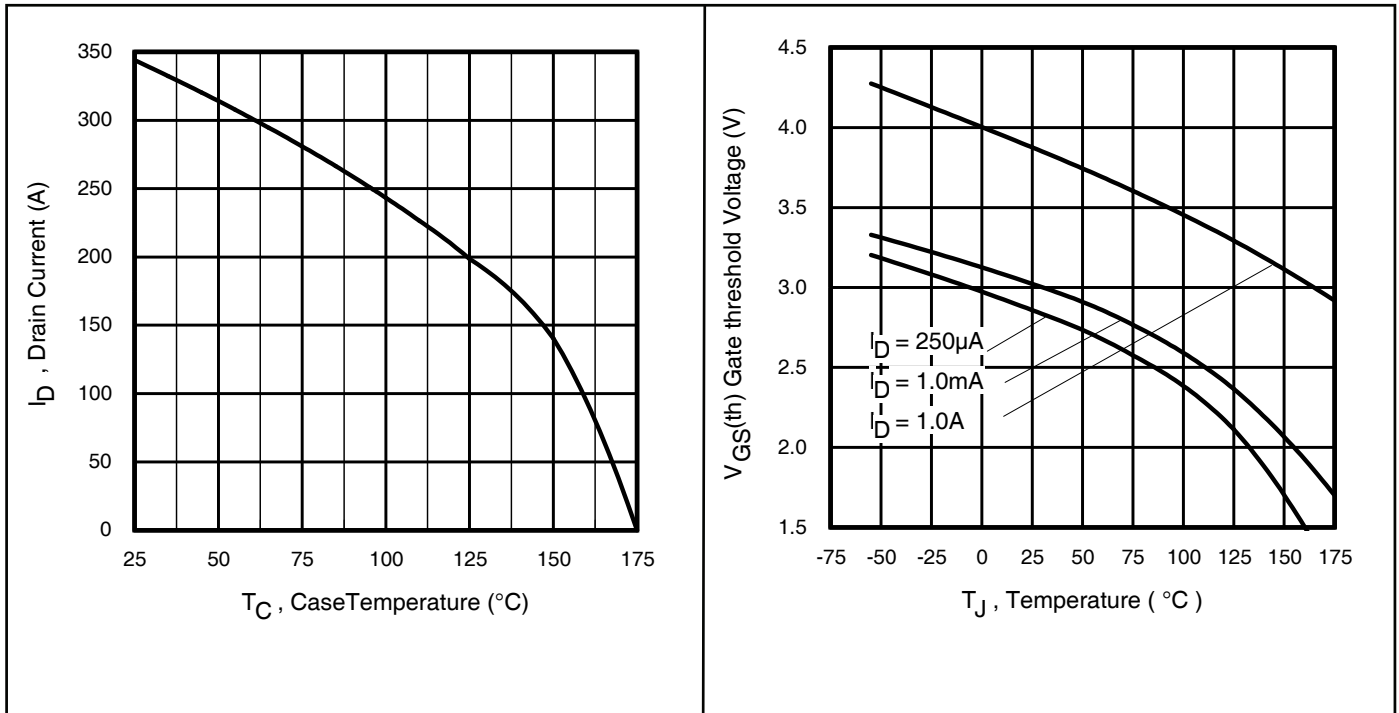


Figure 11 Maximum Drain Current vs. Case Temperature

Figure 12 Typical Threshold Voltage vs. Junction Temperature

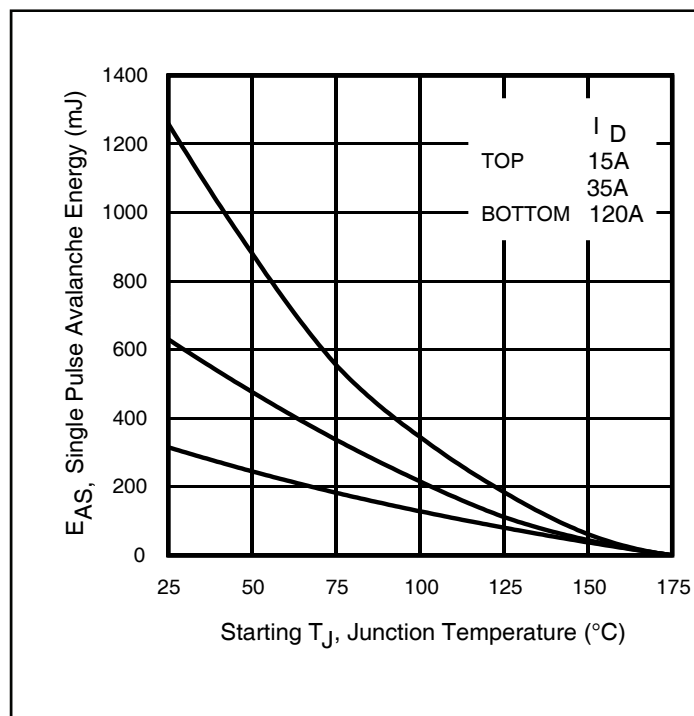


Figure 13 Maximum Avalanche Energy vs. Temperature



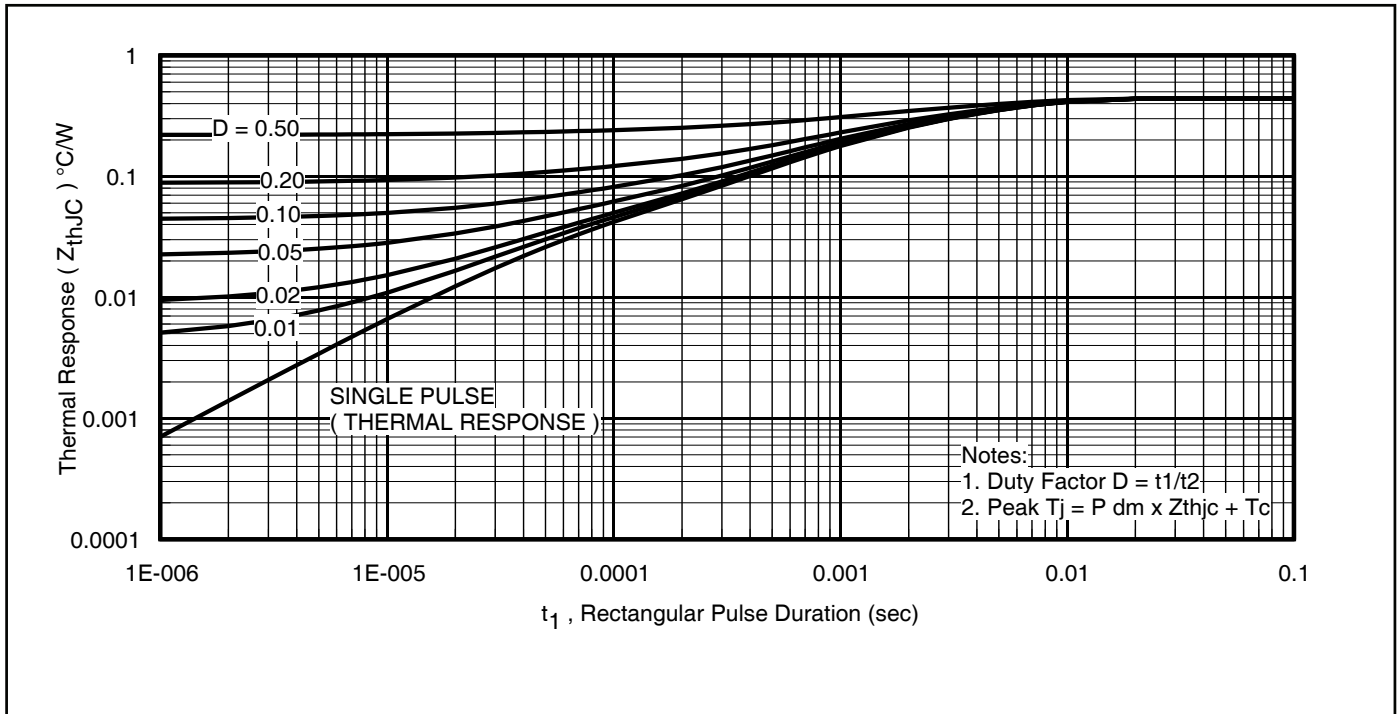


Figure 14 Maximum Effective Transient Thermal Impedance, Junction-to-Case

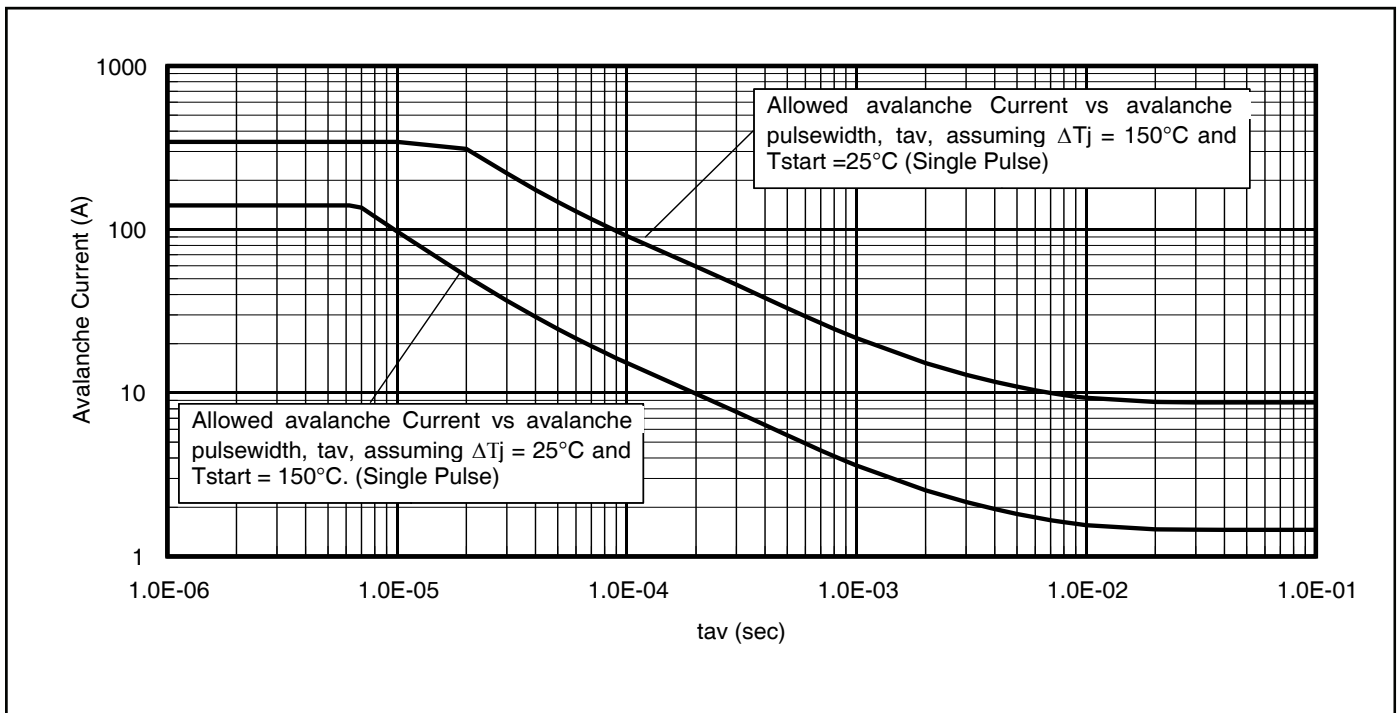
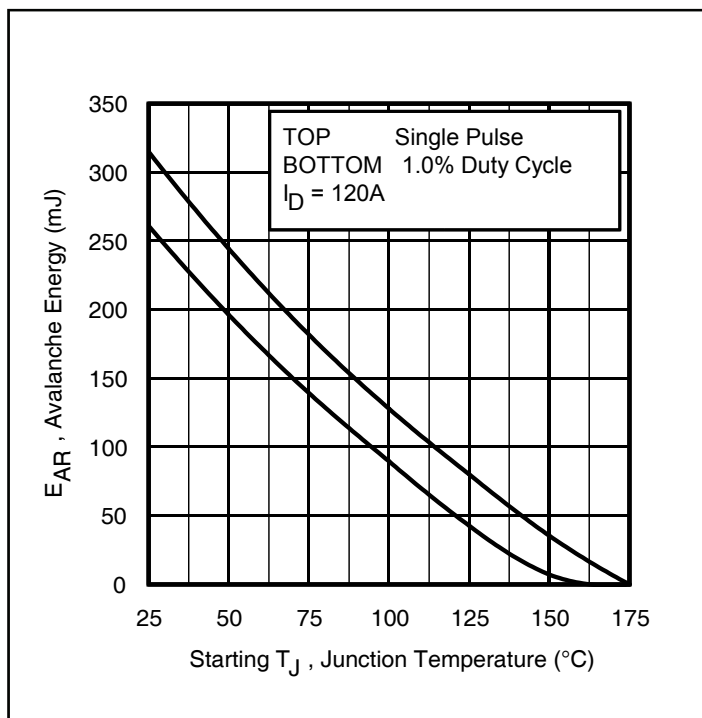


Figure 15 Typical Avalanche Current vs. Pulse Width



**Notes on Repetitive Avalanche Curves , Figures 15, 16:**  
**(For further info, see AN-1005 at [www.infineon.com](http://www.infineon.com))**

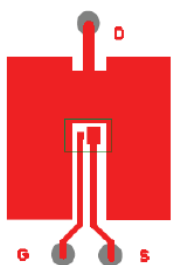
1. Avalanche failures assumption:  
 Purely a thermal phenomenon and failure occurs at a temperature far in excess of  $T_{jmax}$ . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as  $T_{jmax}$  is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 19a, 19b.
4.  $P_{D(ave)}$  = Average power dissipation per single avalanche pulse.
5.  $BV$  = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6.  $I_{av}$  = Allowable avalanche current.
7.  $DT$  = Allowable rise in junction temperature, not to exceed  $T_{jmax}$  (assumed as 25°C in Figure 14, 15).  
 $t_{av}$  = Average time in avalanche.  
 $D$  = Duty cycle in avalanche =  $t_{av} \cdot f$   
 $Z_{thJC}(D, t_{av})$  = Transient thermal resistance, see Figures 14)  
 $P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$   
 $I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$   
 $E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$

**Figure 16 Maximum Avalanche Energy vs. Temperature**

**Notes:**

- ② Used double sided cooling , mounting pad with large heatsink
- ③ Mounted on minimum footprint full size board with metalized back and with small clip heatsink.

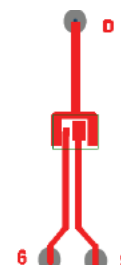
④ TC measured with thermocouple mounted to top (Drain) of part.



① Surface mounted on 1 in. square Cu board (still air).



② Mounted to a PCB with small clip heatsink (still air).



③ Mounted on minimum footprint full size board with metalized back and with small clip heatsink (still air)

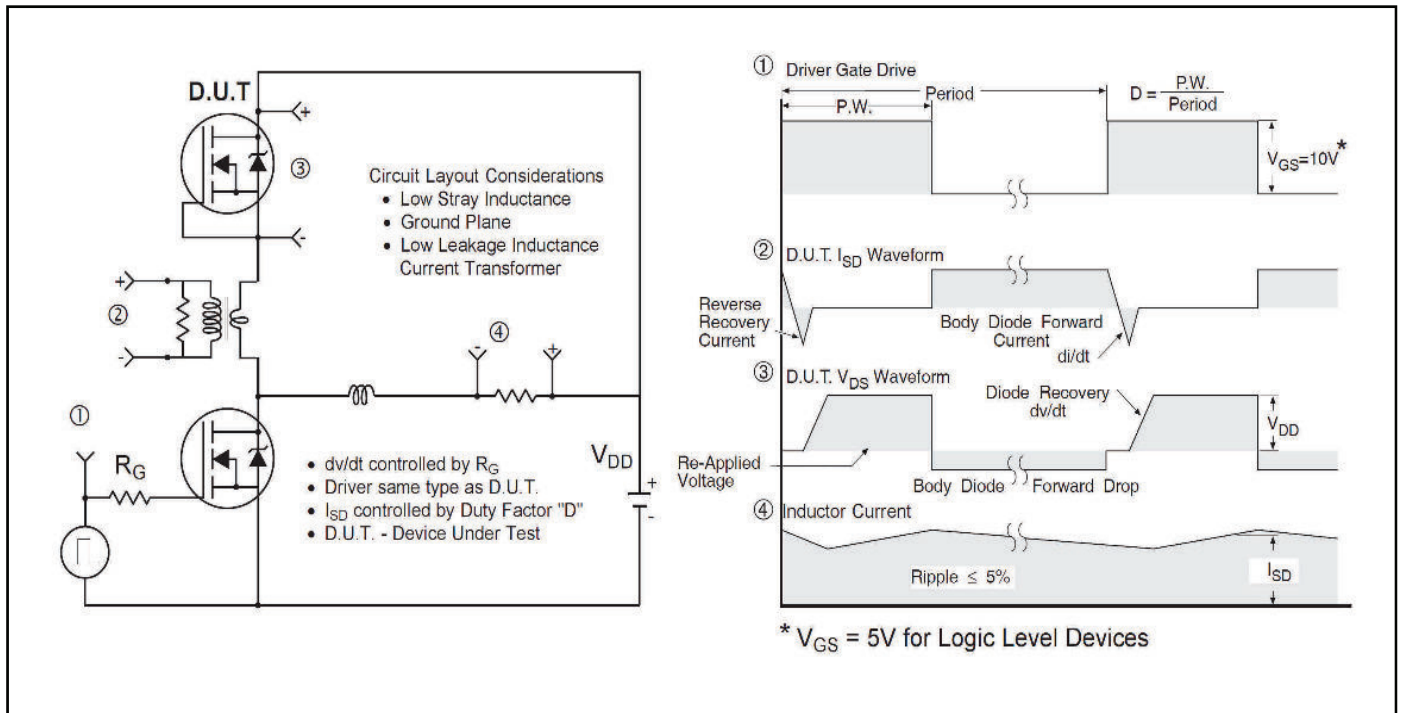


Figure 17 Peak Diode Recovery  $dv/dt$  Test Circuit for N-Channel HEXFET™ Power MOSFETs

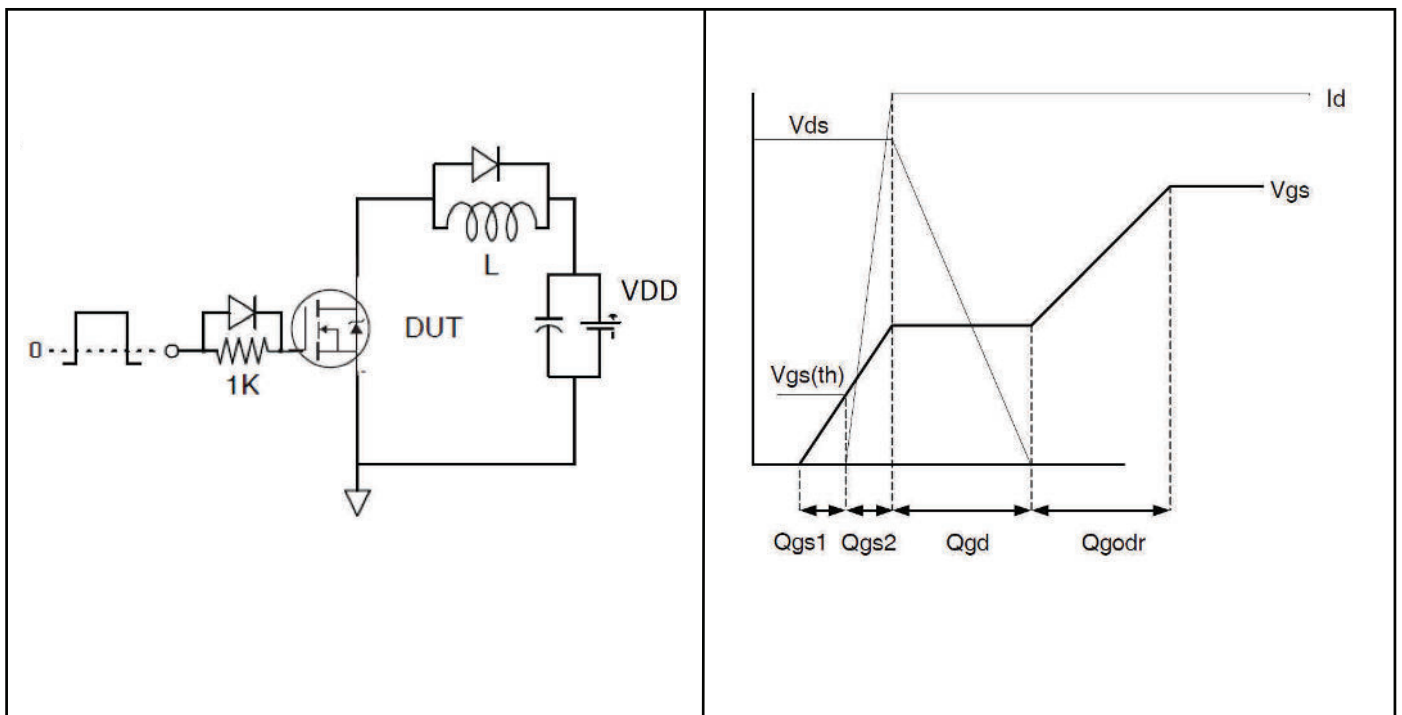


Figure 18a Gate Charge Test Circuit

Figure 18b Gate Charge Waveform

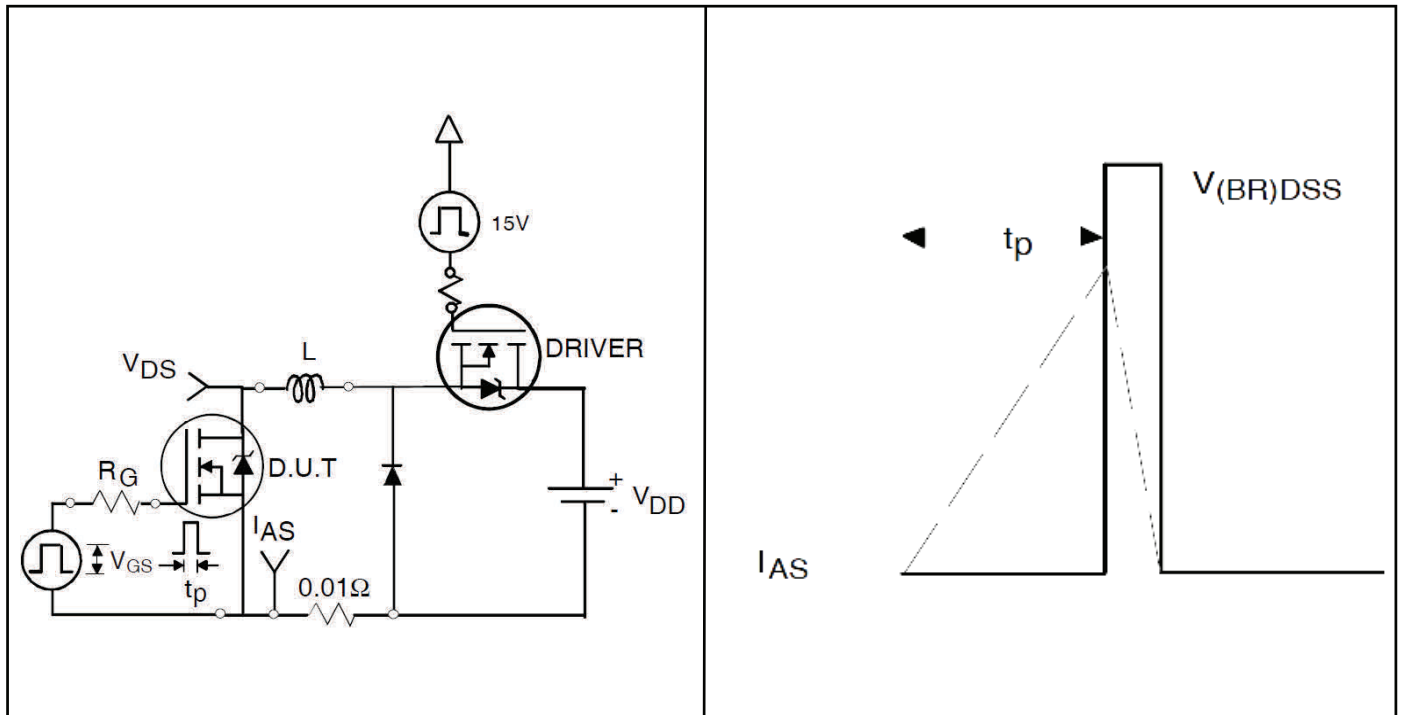


Figure 19a Unclamped Inductive Test Circuit

Figure 19b Unclamped Inductive Waveforms

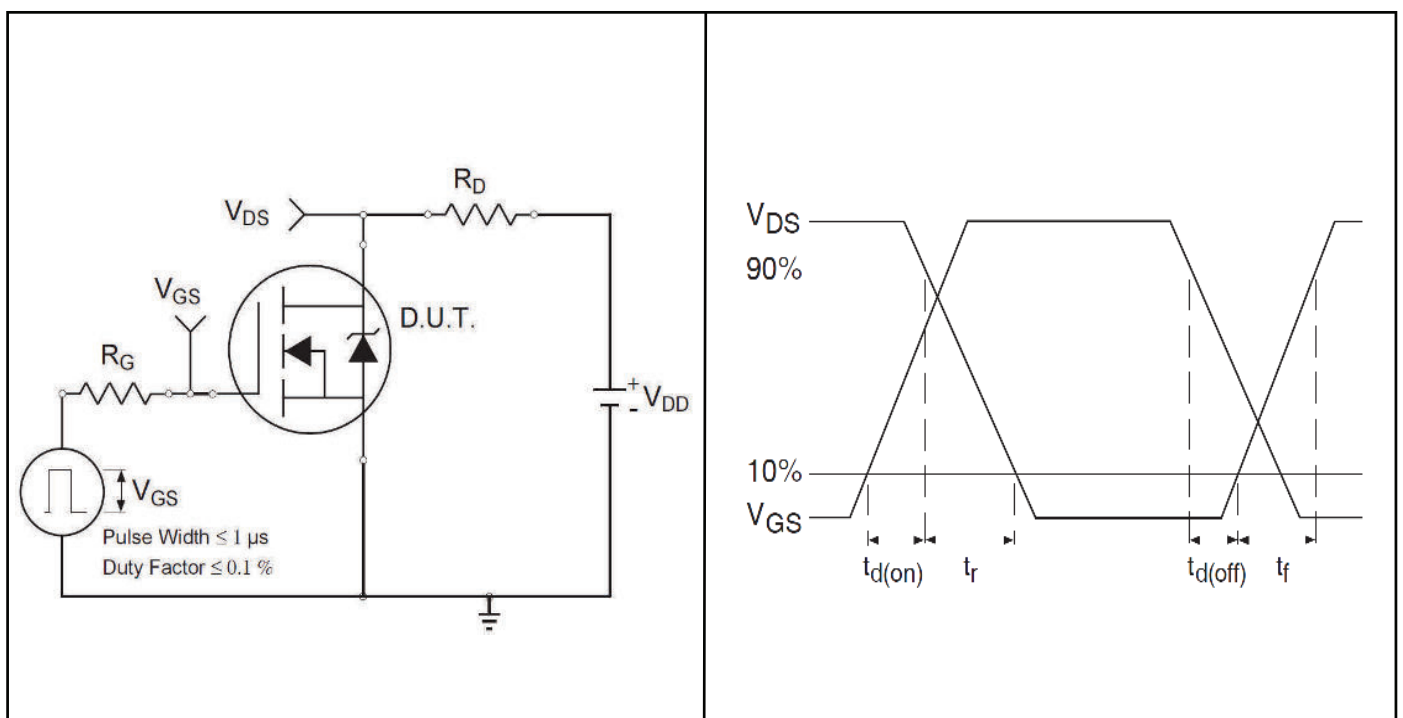


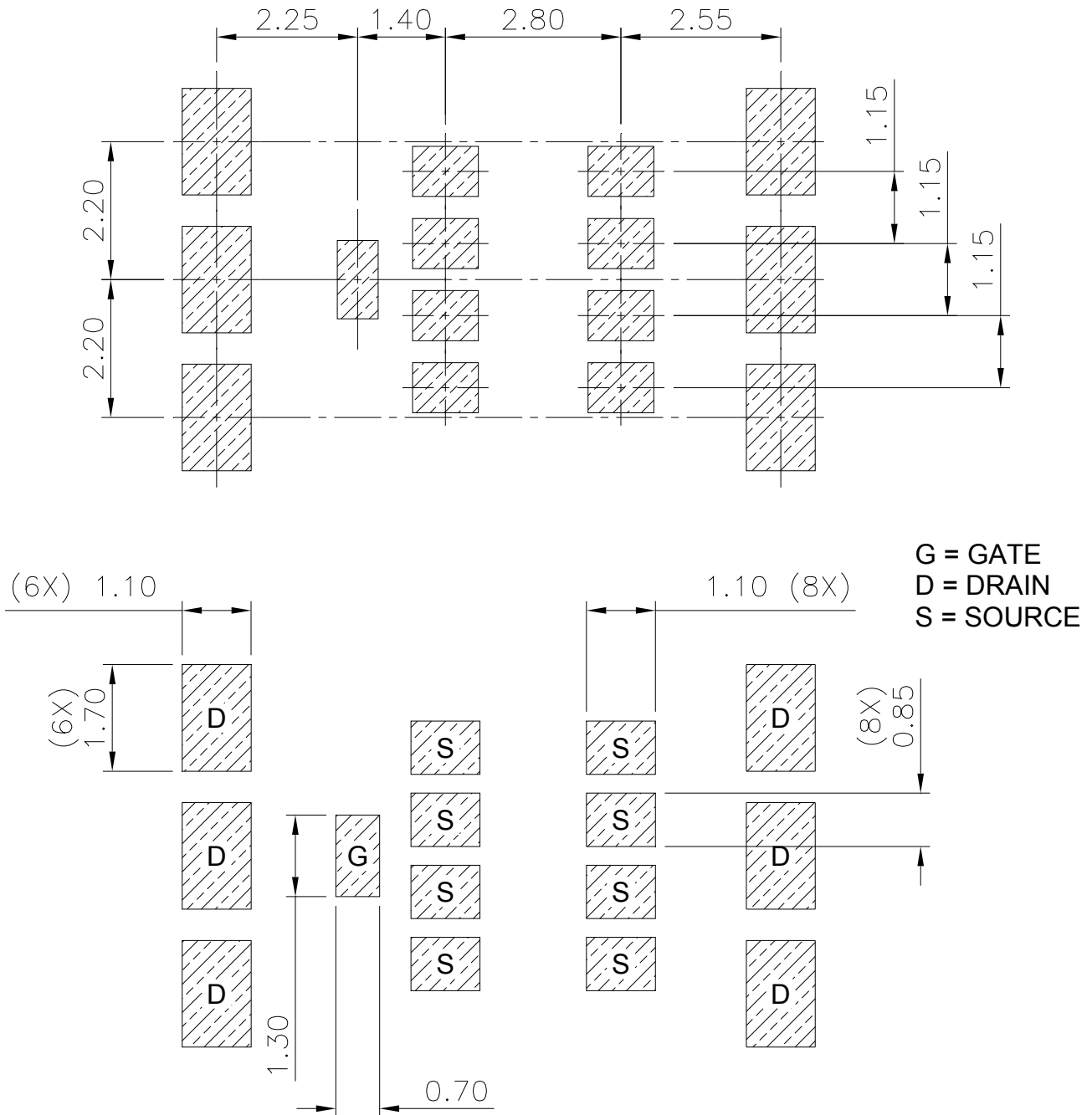
Figure 20a Switching Time Test Circuit

Figure 20b Switching Time Waveforms

## 5 Package Information

### DirectFET™ Board Footprint, L8 Outline (Large Size Can, 8-Source Pads)

Please see DirectFET™ application note [AN-1035](#) for all details regarding the assembly of DirectFET™. This includes all recommendations for stencil and substrate designs.

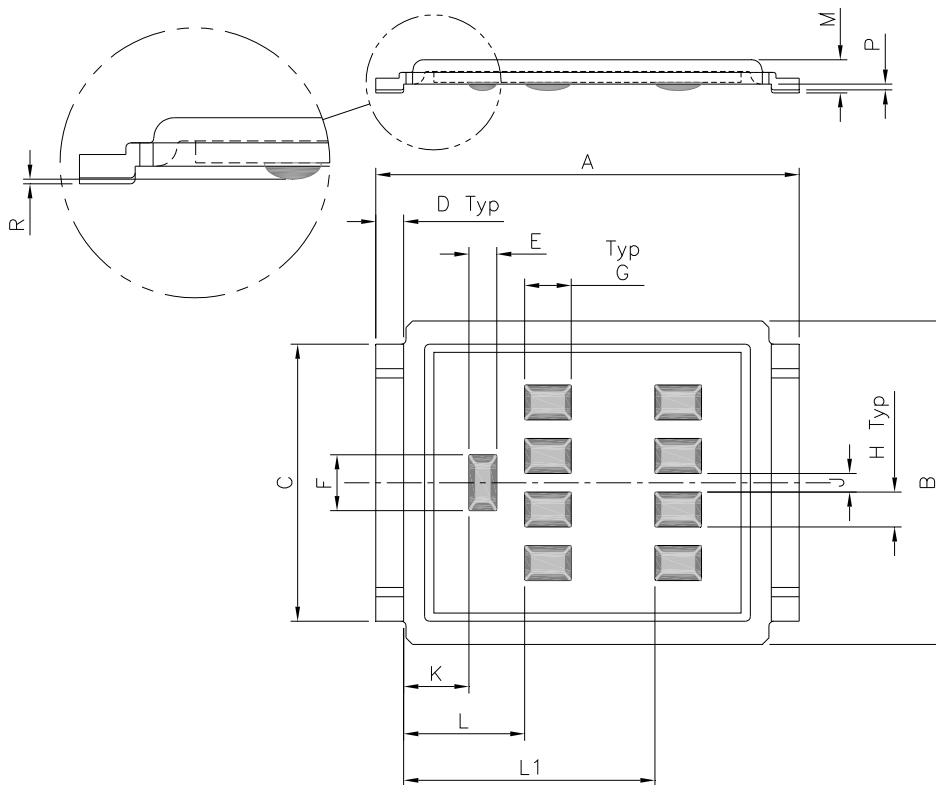


IRF7749L1TRPbF

Package Information

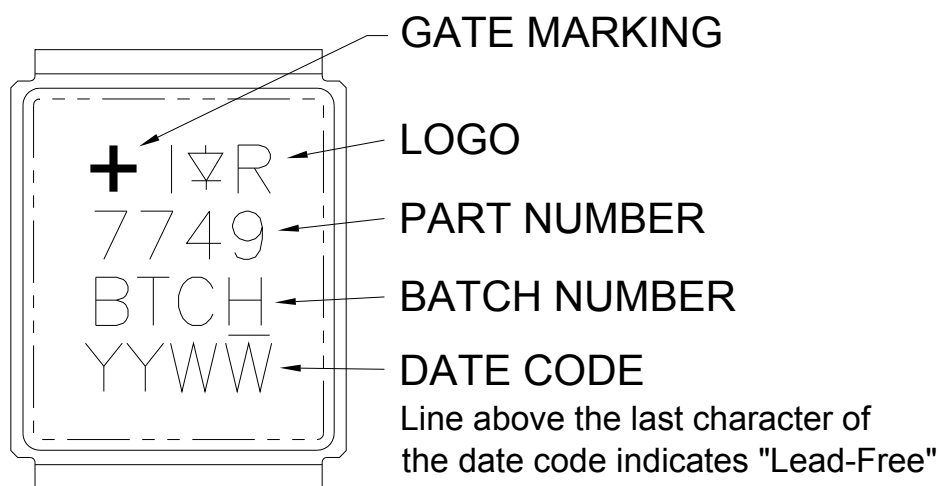
DirectFET™ Outline Dimension, L8 Outline  
(Large Size Can, 8-Source Pads)

Please see DirectFET™ application note [AN-1035](#) for all details regarding the assembly of DirectFET™. This includes all recommendations for stencil and substrate designs.



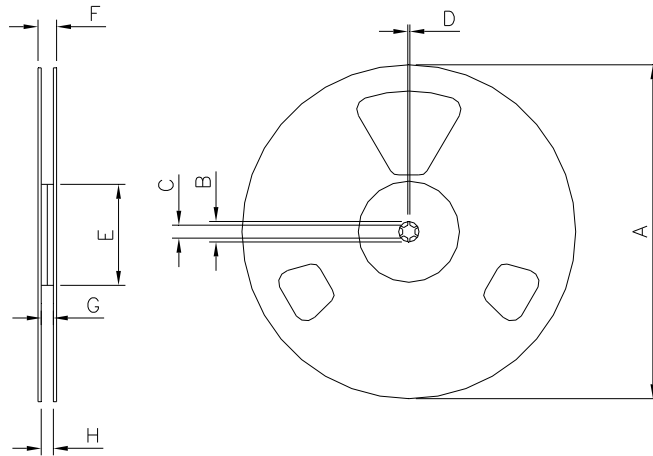
CODE	METRIC		IMPERIAL	
	MIN	MAX	MIN	MAX
A	9.05	9.15	0.356	0.360
B	6.85	7.10	0.270	0.280
C	5.90	6.00	0.232	0.236
D	0.55	0.65	0.022	0.026
E	0.58	0.62	0.023	0.024
F	1.18	1.22	0.046	0.048
G	0.98	1.02	0.039	0.040
H	0.73	0.77	0.029	0.030
J	0.38	0.42	0.015	0.017
K	1.35	1.45	0.053	0.057
L	2.55	2.65	0.100	0.104
L1	5.35	5.45	0.211	0.215
M	0.68	0.74	0.027	0.029
P	0.09	0.17	0.003	0.007
R	0.02	0.08	0.001	0.003

DirectFET™ Part Marking



Tape & Reel Information

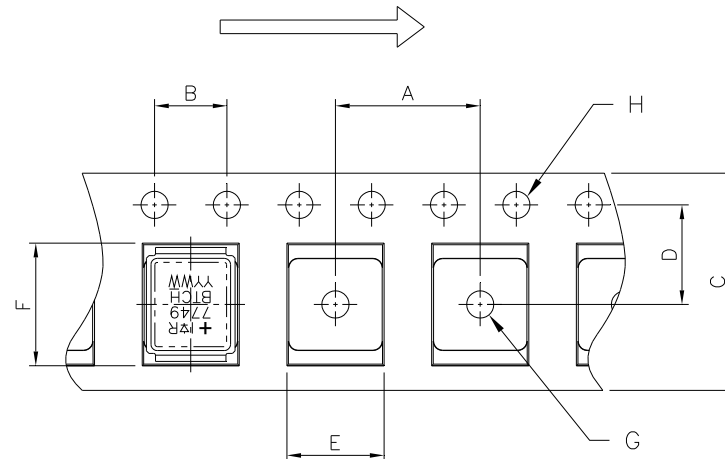
DirectFET™ Tape & Reel Dimension (Showing component orientation).



NOTE: Controlling dimensions in mm  
Std reel quantity is 4000 parts. (ordered as IRF7749L1TRPBF).

REEL DIMENSIONS				
STANDARD OPTION (QTY 4000)				
	METRIC		IMPERIAL	
CODE	MIN	MAX	MIN	MAX
A	330.00	N.C	12.992	N.C
B	20.20	N.C	0.795	N.C
C	12.80	13.20	0.504	0.520
D	1.50	N.C	0.059	N.C
E	99.00	100.00	3.900	3.940
F	N.C	22.40	N.C	0.880
G	16.40	18.40	0.650	0.720
H	15.90	19.40	0.630	0.760

LOADED TAPE FEED DIRECTION



NOTE: CONTROLLING DIMENSIONS IN MM

DIMENSIONS				
	METRIC		IMPERIAL	
CODE	MIN	MAX	MIN	MAX
A	11.90	12.10	4.69	0.476
B	3.90	4.10	0.154	0.161
C	15.90	16.30	0.623	0.642
D	7.40	7.60	0.291	0.299
E	7.20	7.40	0.283	0.291
F	9.90	10.10	0.390	0.398
G	1.50	N.C	0.059	N.C
H	1.50	1.60	0.059	0.063

## 6 Qualification Information

### Qualification Information

<b>Qualification Level</b>	Industrial (per JEDEC JESD47F) †	
<b>Moisture Sensitivity Level</b>	DirectFET™ Large Can	MSL1 (per JEDEC J-STD-020D)†
<b>RoHS Compliant</b>	Yes	

† Applicable version of JEDEC standard at the time of product release.



## Revision History

### Major changes since the last revision

Page or Reference	Revision	Date	Description of changes
All pages	2.0	2013-01-07	• First release Final data sheet.
All pages	2.1	2013-02-13	• TR1 option removed and Tape & Reel Info updated accordingly. • Hyperlinks added throw-out the document
All pages	2.2	2019-02-20	• Update to R-Theta.

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